Product data sheet

1. General description

NPN low V_{CEsat}transistor in a SOT323 (SC-70) Surface Mounted Device (SMD) plastic package.

PNP complement: PBSS5160U

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- · High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

3. Applications

- High voltage DC-to-DC conversion
- High voltage MOSFET gate driving
- · High voltage motor control
- · High voltage power switches (e.g. motors, fans)
- · Automotive applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	60	V
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms	-	-	1	Α
I _{CM}	peak collector current		-	-	2	А
R _{CEsat}	collector-emitter saturation resistance	I_C = 1 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	230	280	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	□ 3	
2	Е	emitter		C
3	С	collector		В
			SC-70 (SOT323)	 E sym123

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS4160U	SC-70	plastic, surface-mounted package; 3 leads; 1.3 mm pitch; 2 mm x 1.25 mm x 0.95 mm body	SOT323		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS4160U	52%

^{[1] % =} placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	80	V
V _{CEO}	collector-emitter voltage	open base		-	60	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
Ic	collector current		[1]	-	750	mA
			[2]	-	930	mA
			[3]	-	1	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	2	Α
I _B	base current			-	300	mA
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	250	mW
			[2]	-	350	mW
			[3]	-	415	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C

PBSS4160U

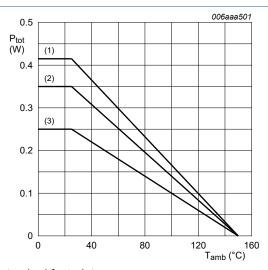
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Symbol	Parameter	Conditions	Min	Max	Unit
T _{stg}	storage temperature		-65	150	°C

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm 2 . Device mounted on a ceramic PCB, Al₂O₃, standard footprint.
- [3]



- (1) Ceramic PCB, Al₂O₃, standard footprint
 (2) FR4 PCB, mounting pad for collector 1 cm²
 (3) FR4 PCB, standard footprint

Fig. 1. **Power derating curves**

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uig-a)	thermal resistance from junction to ambient		[1]	-	-	500	K/W
			[2]	-	-	357	K/W
			[3]	-	-	301	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	150	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

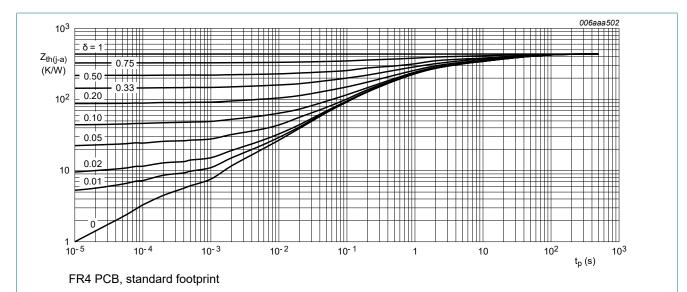


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

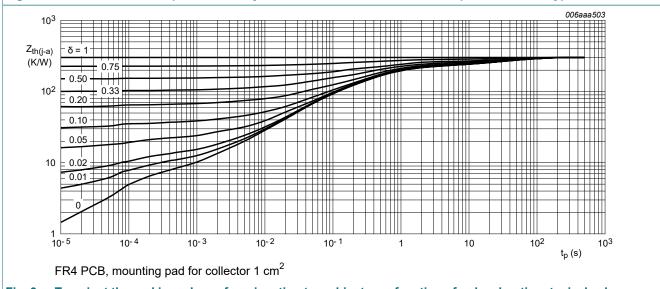
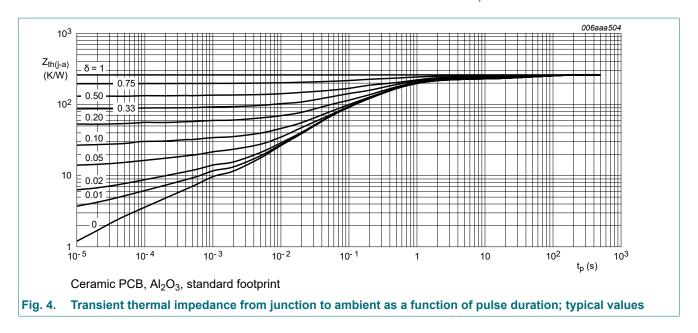


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 60 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	$V_{CB} = 60 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = 60 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 1 mA; T _{amb} = 25 °C	250	500	-	
		V_{CE} = 5 V; I_{C} = 500 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	420	-	
		V_{CE} = 5 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	180	-	
V _{CEsat}	collector-emitter	I _C = 100 mA; I _B = 1 mA; T _{amb} = 25 °C	-	90	115	mV
	saturation voltage	I_C = 500 mA; I_B = 50 mA; T_{amb} = 25 °C	-	120	150	mV
		$I_C = 1 \text{ A}$; $I_B = 100 \text{ mA}$; pulsed; $t_p \le$	-	230	280	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	230	280	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.95	1.1	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 5 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.85	0.9	V
t _d	delay time	I _C = 0.5 A; I _{Bon} = 25 mA; I _{Boff} = -25 mA;	-	11	-	ns
t _r	rise time	T _{amb} = 25 °C	-	78	-	ns
t _{on}	turn-on time		-	90	-	ns
t _s	storage time		-	340	-	ns
t _f	fall time		-	160	-	ns
t _{off}	turn-off time		-	500	-	ns
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 50 mA; f = 100 MHz; T_{amb} = 25 °C	150	220	-	MHz

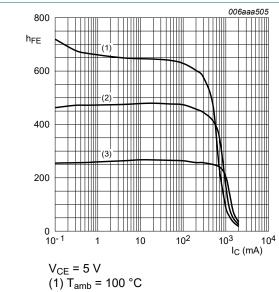
PBSS4160U

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60 V, 1 A NPN low VCEsat transistor

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz};$	-	5.5	10	pF
		T _{amb} = 25 °C				



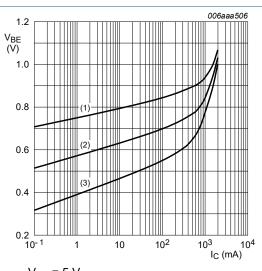
(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \text{ °C}$$

(3) $T_{amb} = -55 \text{ °C}$

DC current gain as a function of collector Fig. 5. current; typical values

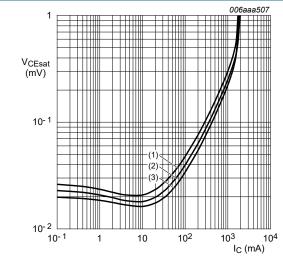


$$V_{CE} = 5 V$$

$$(1) T_{amb} = -55 °C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

Base-emitter voltage as a function of collector Fig. 6. current; typical values



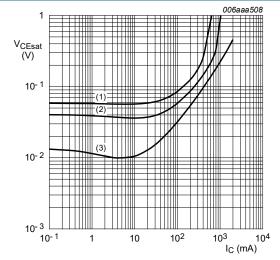
$$I_{\rm C}/I_{\rm B} = 20$$

$$I_C/I_B = 20$$
 (1) $T_{amb} = 100 \, ^{\circ}C$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \,^{\circ}C$$

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

$$T_{amb} = 25 \, ^{\circ}C$$

(1) $I_{C}/I_{B} = 100$

(2)
$$I_C/I_B = 50$$

$$(3) I_{\rm C}/I_{\rm B} = 10$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

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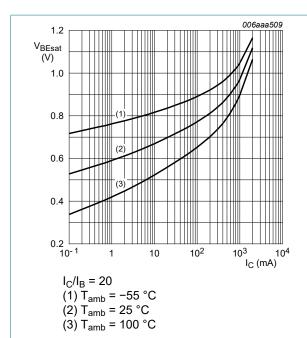
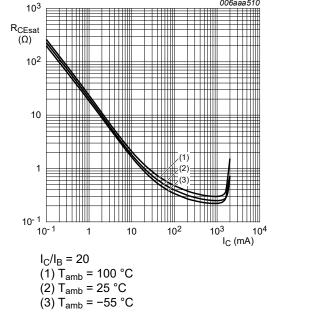


Fig. 9. collector current; typical values



Base-emitter saturation voltage as a function of Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

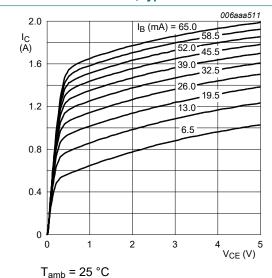
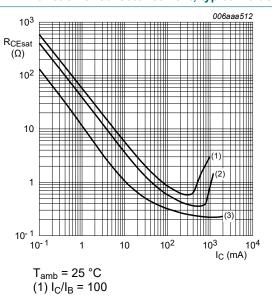


Fig. 11. Collector current as a function of collectoremitter voltage; typical values

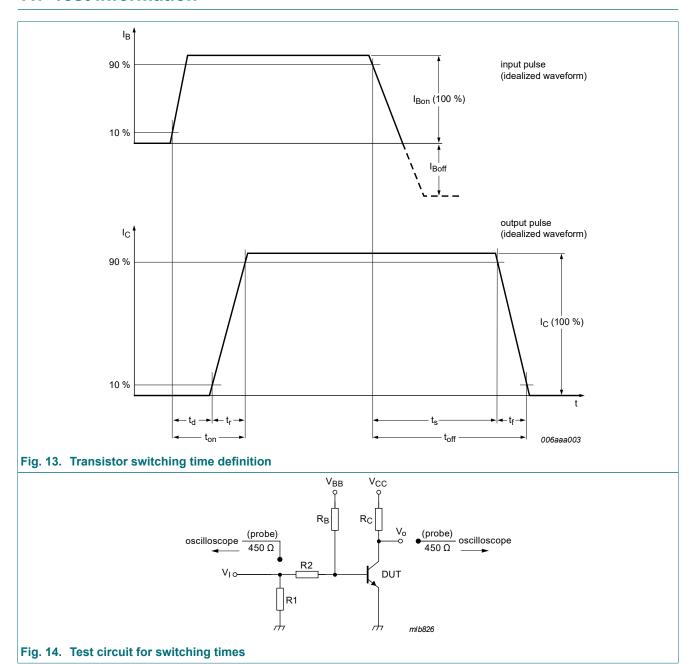


 $(2) I_{\rm C}/I_{\rm B} = 50$ (3) $I_C/I_B = 10$

Fig. 12. Collector-emitter saturation resistance as a function of collector current; typical values

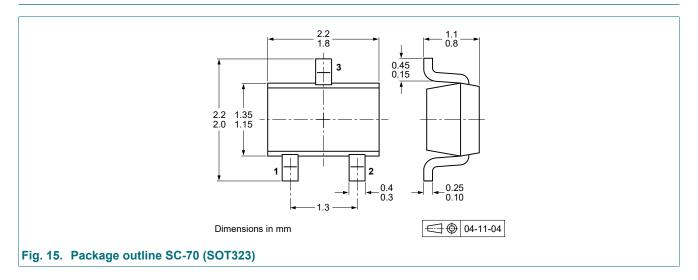
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11. Test information



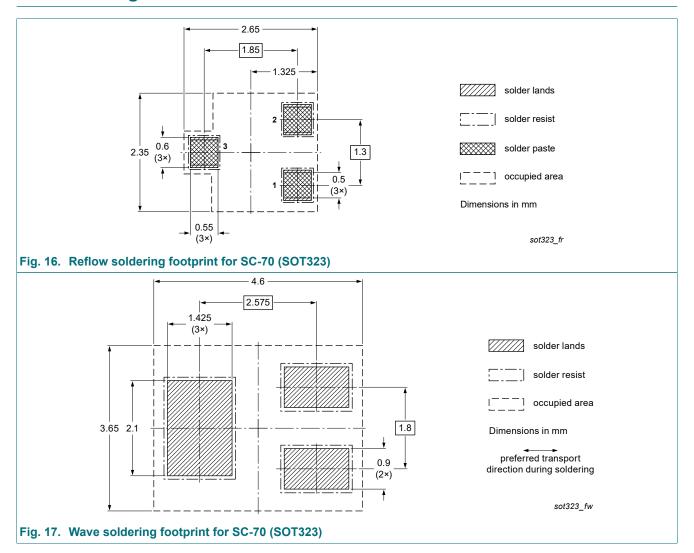
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Table 0. INEVISION III	otor y			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4160U v.4	20250804	Product data sheet	-	PBSS4160U v.3
Modifications	Nexperia.	this data sheet has been rede ve been adapted to the new o		, ,
PBSS4160U v.3	20091211	Product data sheet	-	PBSS4160U v.2
PBSS4160U v.2	20050719	Product data sheet	-	PBSS4160U v.1
PBSS4160U v.1	20040423	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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